



Power Transistor(60V,3A)

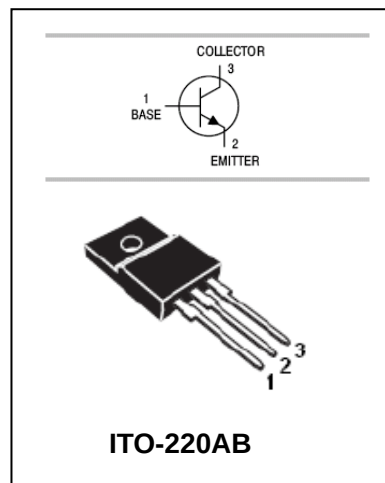
2SD2061

FEATURES

- Low saturation voltage, typically $V_{CE(sat)}=0.3V$ at $I_C/I_B=2A/0.2A$
- Excellent DC current gain characteristics.
- $P_C=30W.(T_C=25^{\circ}C)$



Lead-free



MAXIMUM RATING operating temperature range applies unless otherwise specified

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	DC Pulse	A
P_C	Collector Dissipation	$T_a=25^{\circ}C$ $T_C=25^{\circ}C$	W
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	$^{\circ}C$



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ELECTRICAL CHARACTERISTICS Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Test conditions	MIN	Typ	MAX	UNIT
Collector-base Breakdown Voltage	BV_{CBO}	$I_C=50\mu A, I_B=0$	80			V
Collector-emitter Breakdown Voltage	BV_{CEO}	$I_C=1mA, I_B=0$	60			V
Emitter-base Breakdown Voltage	BV_{EBO}	$I_E=50\mu A, I_C=0$	5			V
Collector Cut-off Current	I_{CBO}	$V_{CB}=60V, I_E=0$			10	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=4V, I_C=0$			10	μA
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=0.5A$	100		320	
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2A, I_B=0.2A$			1	V
Base-emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=2A, I_B=0.2A$			1.5	V
Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		70		pF
Transition Frequency	f_T	$V_{CE}=5V, I_E=-0.5A$ $f=5MHz$		8		MHz

CLASSIFICATION OF h_{FE}

Range	100-320
Marking	EF

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PACKAGE OUTLINE

Plastic surface mounted package

ITO-220AB

